

BSS63LT1G, NSVBSS63LT1G

High Voltage Transistor

PNP Silicon

Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CEO}	-100	Vdc
Collector – Emitter Voltage $R_{BE} = 10\text{ k}\Omega$	V_{CER}	-110	Vdc
Collector Current – Continuous	I_C	-100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

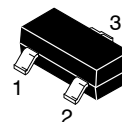
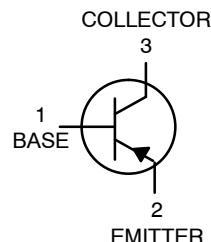
1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



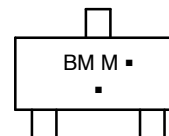
ON Semiconductor®

<http://onsemi.com>



SOT-23
CASE 318
STYLE 6

MARKING DIAGRAM



BM = Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
BSS63LT1G	SOT-23 (Pb-free)	3000 / Tape & Reel
NSVBSS63LT1G	SOT-23 (Pb-free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BSS63LT1G, NSVBSS63LT1G

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector – Emitter Breakdown Voltage ($I_C = -100\ \mu\text{Adc}$)	$V_{(BR)CEO}$	-100	–	–	Vdc
Collector – Emitter Breakdown Voltage ($I_C = -10\ \mu\text{Adc}$, $I_E = 0$, $R_{BE} = 10\ \text{k}\Omega$)	$V_{(BR)CER}$	-110	–	–	Vdc
Collector – Base Breakdown Voltage ($I_E = -10\ \mu\text{Adc}$, $I_C = 0$)	$V_{(BR)CBO}$	-110	–	–	Vdc
Emitter – Base Breakdown Voltage ($I_E = -10\ \mu\text{Adc}$)	$V_{(BR)EBO}$	-6.0	–	–	Vdc
Collector Cutoff Current ($V_{CB} = -90\ \text{Vdc}$, $I_E = 0$)	I_{CBO}	–	–	-100	nAdc
Collector Cutoff Current ($V_{CE} = -110\ \text{Vdc}$, $R_{BE} = 10\ \text{k}\Omega$)	I_{CER}	–	–	-10	μAdc
Emitter Cutoff Current ($V_{EB} = -6.0\ \text{Vdc}$, $I_C = 0$)	I_{EBO}	–	–	-200	nAdc

ON CHARACTERISTICS

DC Current Gain ($I_C = -10\ \text{mAdc}$, $V_{CE} = -1.0\ \text{Vdc}$) ($I_C = -25\ \text{mAdc}$, $V_{CE} = -1.0\ \text{Vdc}$)	h_{FE}	30 30	– –	– –	–
Collector – Emitter Saturation Voltage ($I_C = -25\ \text{mAdc}$, $I_B = -2.5\ \text{mAdc}$)	$V_{CE(sat)}$	–	–	-250	mVdc
Base – Emitter Saturation Voltage ($I_C = -25\ \text{mAdc}$, $I_B = -2.5\ \text{mAdc}$)	$V_{BE(sat)}$	–	–	-900	mVdc

SMALL-SIGNAL CHARACTERISTICS

Current – Gain – Bandwidth Product ($I_C = -25\ \text{mAdc}$, $V_{CE} = -5.0\ \text{Vdc}$, $f = 20\ \text{MHz}$)	f_T	50	95	–	MHz
Case Capacitance ($I_E = I_C = 0$, $V_{CB} = -10\ \text{Vdc}$, $f = 1.0\ \text{MHz}$)	C_C	–	–	20	pF

1. FR-5 = $1.0 \times 0.75 \times 0.062\ \text{in.}$
2. Alumina = $0.4 \times 0.3 \times 0.024\ \text{in.}$ 99.5% alumina.

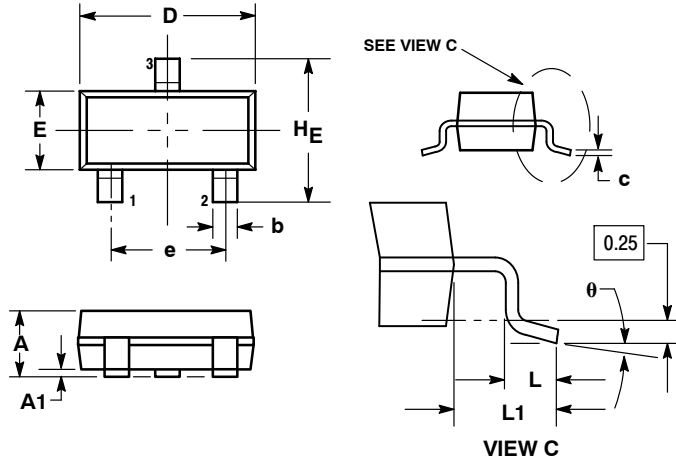
BSS63LT1G, NSVBSS63LT1G

PACKAGE DIMENSIONS

SOT-23 (TO-236)

CASE 318-08

ISSUE AP



NOTES:

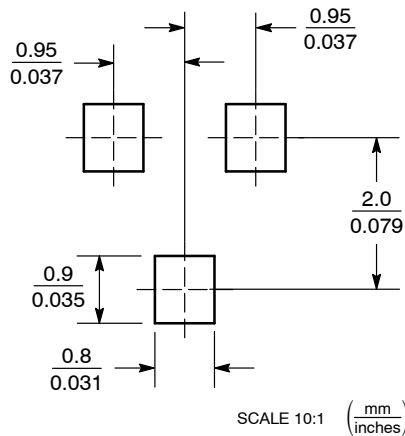
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

STYLE 6:

1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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